



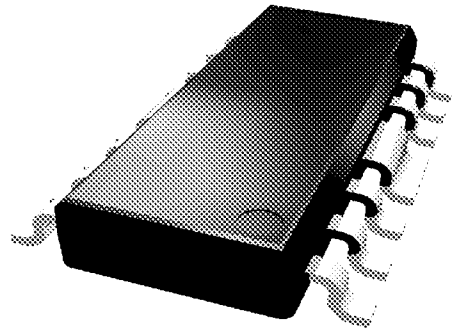
ADA10001S3C
 Linear Amplifier MMIC
 Data Sheet - Rev. 1

FEATURES

- High Linearity ($IIP_3 + 18 \text{ dBm}$)
- Low Noise Figure (2.0 dB)
- Single Supply (+8Vdc)
- Wide Bandwidth (50MHz - 1 GHz)

APPLICATIONS

- Driver Amplifier
- CATV - Distribution / Drop Amplifiers



S3C
16 Pin SOIC Package

DESCRIPTION:

The ADA10001 is a monolithic IC intended for use in applications requiring high linearity such as: Cellular Telephone Base Station Driver Amplifiers, CATV Fiber Receiver/Distribution Amplifiers and CATV Drop Amplifiers. Supplied in a surface mount, 16 lead-SOIC package, it is well suited for use in amplifiers where small size, reduced component count, and high reliability are important.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	MIN.	MAX.	UNITS
V_{DD}/V_{RFOUT}	0	12	V_{DC}
V_{RFIN}		0	V_{DC}
RF_{IN}		+ 10	dBm
Storage Temperature	- 65	+150	°C
Soldering Temperature		260	°C
Soldering Time		5.0	Sec.
Thermal Resistance		35	°C/W

ELECTRICAL SPECIFICATIONS(T_A = +25 °C, RF = 50 to 1000 MHz, Test System = 75Ω, V_{DD} = +8V_{DC})

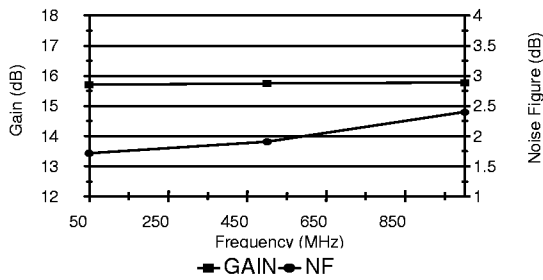
PARAMETER	MIN.	TYP.	MAX.	UNITS
CSO ²	60			dBc
CTB ²	65			dBc
Gain	14	15		dB
Noise Figure		2.0	3.5	dB
2nd Order Input Intercept Point (IIP2) ³	+35	+38		dBm
3rd Order Input Intercept Point (IIP3) ³	+15	+18		dBm

1. The device can be operated at +6 V_{DC} for lower power dissipation; Refer to the figures on page 3 for performance variation with supply voltage.
2. 160 channels, +23 dBmV per channel, (measured at the output) 6 MHz channel spacing.
3. Two tones, -10 dBm per tone at input.

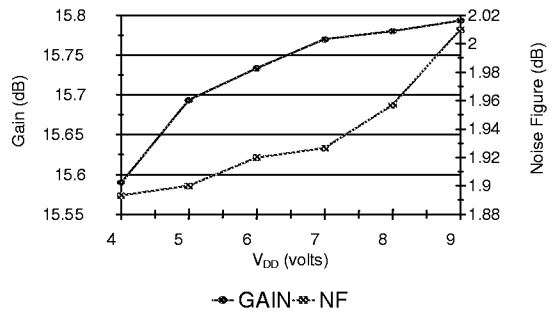
OPERATING RANGES

PARAMETER	MIN.	TYP.	MAX.	UNITS
V _{DD}	4	8 ¹	9	Volts
I _{DD}	50	-	150	mA
Case Temperature	-40	-	70*	°C

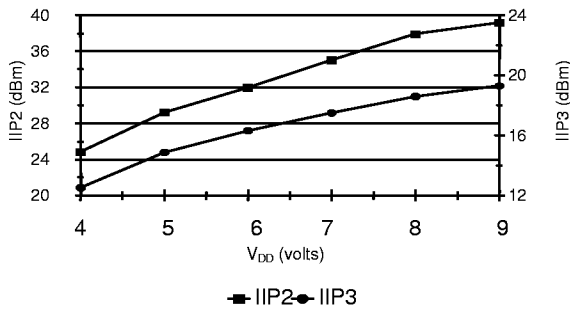
Gain and Noise Figure vs Frequency
 Tc = 25 deg C, V_{DD} = +8V



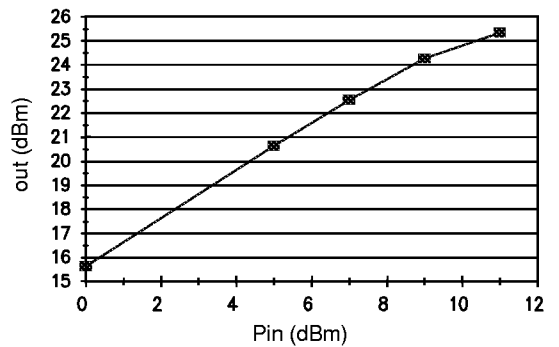
Gain and Noise Figure vs. V_{DD}
 Tc = 25 deg C, RF = 500 MHz



IIP2, IIP3 vs. V_{DD}
 Tc = 25 deg C

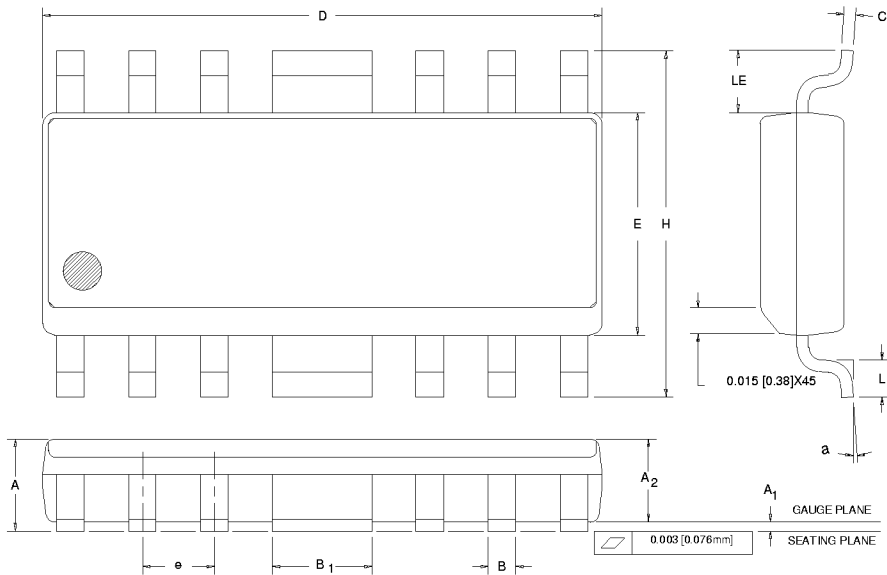


Pin vs. Pout
 Tc = 25 deg C, V_{DD} = +8V, RF = 500 MHz



* Notes:

- IIP2 Measured at 986.5 MHz, Input = two tones (55.25 MHz and 931.25 MHz) at - 10 dBm.
- IIP3 Measured at 986.5 MHz, Input = two tones (986.5 MHz and 992.5 MHz) at - 10 dBm.



S _M Q _L	INCHES		MILLIMETERS		NOTE
	MIN	MAX	MIN	MAX	
A	0.058	0.068	1.47	1.73	
A ₁	0.004	0.010	0.10	0.25	
A ₂	0.055	0.065	1.40	1.65	
B	0.013	0.020	0.33	0.50	
B ₁	0.062	0.070	1.58	1.78	
C	0.008	0.010	0.20	0.25	4
D	0.380	0.400	9.66	10.16	2
E	0.150	0.160	3.81	4.06	3
e	0.050 BSC		1.27 BSC		
H	0.226	0.244	5.74	6.20	
L	0.016	0.040	0.41	1.02	
LE	0.030	—	0.76	—	
a	0	8	0	8	

NOTES:

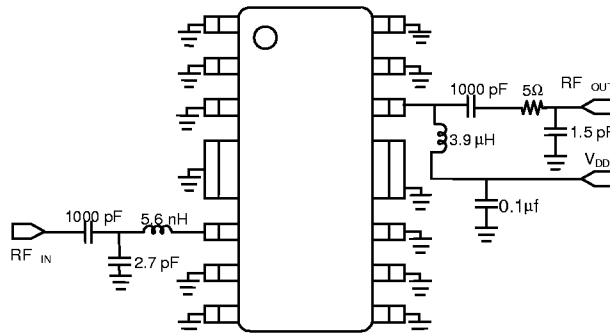
- CONTROLLING DIMENSION: INCHES
- DIMENSION "D" DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS AND GATE BURRS SHALL NOT EXCEED 0.006 [0.15mm] PER SIDE.
- DIMENSION "E" DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSIONS. INTER-LEAD FLASH AND PROTRUSIONS SHALL NOT EXCEED 0.010 [0.25mm] PER SIDE.
- LEAD THICKNESS AFTER PLATING TO BE 0.013 [0.33mm] MAXIMUM.

SPECIFICATION: 98000-006

SUBJECT: PUBLISHED OUTLINE,
16 LEAD BATWING SOIC PKG.

EXTERNAL TEST CIRCUIT

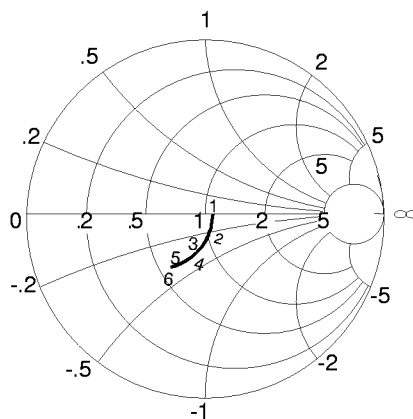
PINFUNCTION	
1	GND
2	GND
3	NC
4	GND
5	GND
6	RF IN
7	NC
8	GND
9	GND
10	NC
11	NC
12	GND
13	GND
14	RF OUT
15	NC
16	GND



INPUT IMPEDANCE

START: 0.050 GHz

STOP: 1.00 GHz



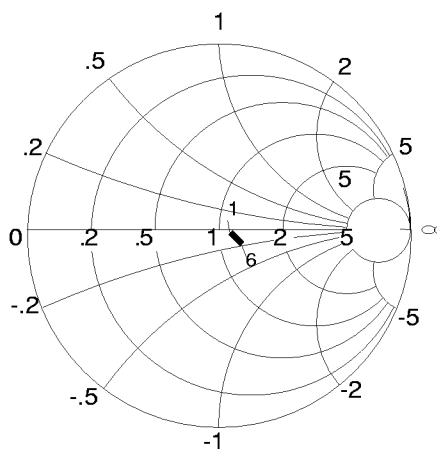
Measured in 75 Ω System

1:	0.050 GHz	79.76 Ω	- 4.79 jΩ
2:	0.20 GHz	77.88 Ω	- 13.21 jΩ
3:	0.40 GHz	70.02 Ω	- 21.83 jΩ
4:	0.6 GHz	59.63 Ω	- 26.56 jΩ
5:	0.8 GHz	49.91 Ω	- 26.56 jΩ
6:	1.0 GHz	41.77 Ω	- 25.15 jΩ

OUTPUT IMPEDANCE

START: 0.050 GHz

STOP: 1.00 GHz



Measured in 75 Ω System

1:	0.050 GHz	83.9 Ω	- 8.1 jΩ
2:	0.20 GHz	84.17 Ω	- 1.19 jΩ
3:	0.40 GHz	85.38 Ω	- 2.27 jΩ
4:	0.6 GHz	87.64 Ω	- 3.82 jΩ
5:	0.8 GHz	90.20 Ω	- 6.60 jΩ
6:	1.0 GHz	93.57 Ω	- 11.76 jΩ